

**AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (currently amended) A gold (Au) alloy bonding wire for a semiconductor device comprising ~~in which at least one of~~ polonium (Po), ~~promethium (Pm), thulium (Tm), and boron (B)~~ is added to high-purity gold having a purity of 99.999% or ~~more~~ greater in an amount of 3-30 parts per million (ppm) by weight and at least one of ~~magnesium (Mg), sodium (Na), vanadium (V), molybdenum (Mo), and technetium (Tc)~~ [[is]] added in an amount of 3-30 ppm by weight to the high-purity gold.

2. (Original) The Au alloy bonding wire of claim 1, wherein palladium (Pd) is further added to the high-purity gold in an amount of 100-1,000 ppm by weight.

3. (Original) The Au alloy bonding wire of claim 1, wherein calcium (Ca) is further added to the high-purity gold in an amount of 30-80 ppm by weight.

4. (Original) The Au alloy bonding wire of claim 1, wherein lanthanum (La) is further added to the high-purity gold in an amount of 20-80 ppm by weight.

5. (Original) The Au alloy bonding wire of claim 2, wherein Ca is further added to the high-purity gold in an amount of 30-80 ppm by weight.

6. (Original) The Au alloy bonding wire of claim 2, wherein La is further added to the high-purity gold in an amount of 20-80 ppm by weight.

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7. (Original) The Au alloy bonding wire of claim 3, wherein La is further added to the high-purity gold in an amount of 20-80 ppm by weight.

8. (Original) The Au alloy bonding wire of claim 5, wherein La is further added to the high-purity gold in an amount of 20-80 ppm by weight.

9. (Original) The Au alloy bonding wire of claim 8, wherein a diameter of the Au alloy bonding wire is 10-50  $\mu\text{m}$ .